

## Power Schottky rectifier

### Features

- High current capability
- Avalanche rated
- Low forward voltage drop current
- High frequency operation

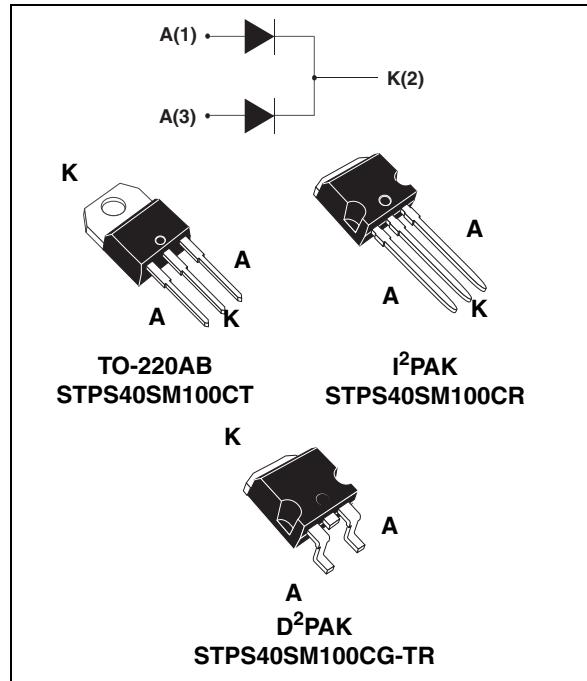
### Description

Schottky rectifier, suited for high frequency switch mode power supply.

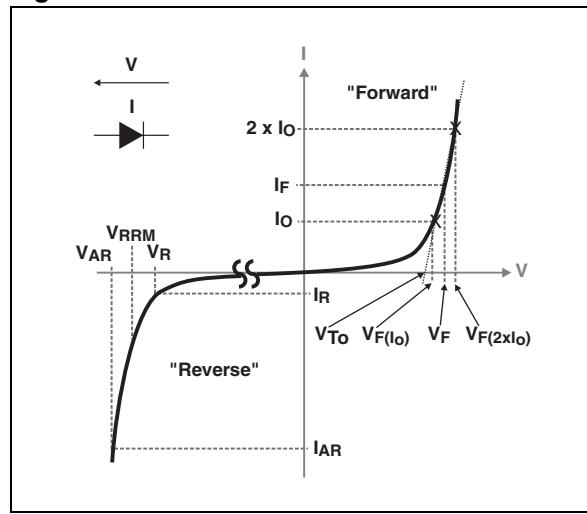
Packaged in TO-220AB, D<sup>2</sup>PAK and I<sup>2</sup>PAK, this device is intended to be used in notebook, game station and desktop adaptors, providing in these applications a good efficiency at both low and high load.

**Table 1. Device summary**

I <sub>F(AV)</sub>	2 x 20 A
V <sub>RRM</sub>	100 V
T <sub>j</sub> (max)	150 °C
V <sub>F</sub> (typ)	0.435 V



**Figure 1. Electrical characteristics (a)**



- a. V<sub>ARM</sub> and I<sub>ARM</sub> must respect the reverse safe operating area defined in [Figure 11](#). V<sub>AR</sub> and I<sub>AR</sub> are pulse measurements ( $t_p < 1 \mu s$ ). V<sub>R</sub>, I<sub>R</sub>, V<sub>RRM</sub> and V<sub>F</sub>, are static characteristics

# 1 Characteristics

**Table 2. Absolute ratings (limiting values)**

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	100	V
I <sub>F(RMS)</sub>	Forward current rms	60	A
I <sub>F(AV)</sub>	Average forward current $\delta = 0.5$	T <sub>c</sub> = 130 °C T <sub>c</sub> = 125 °C	Per diode Per device
			20 40
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal	530
P <sub>ARM</sub> <sup>(1)</sup>	Repetitive peak avalanche power	t <sub>p</sub> = 1 µs T <sub>j</sub> = 25 °C	18000
V <sub>ARM</sub> <sup>(2)</sup>	Maximum repetitive peak avalanche voltage	t <sub>p</sub> < 1 µs T <sub>j</sub> < 150 °C I <sub>AR</sub> < 45 A	120
V <sub>ASM</sub> <sup>(2)</sup>	Maximum single pulse peak avalanche voltage	t <sub>p</sub> < 1 µs T <sub>j</sub> < 150 °C I <sub>AR</sub> < 45 A	120
T <sub>stg</sub>	Storage temperature range	-65 to + 175	°C
T <sub>j</sub>	Maximum operating junction temperature <sup>(3)</sup>	150	°C

1. For temperature or pulse time duration deratings, refer to [Figure 4.](#) and [Figure 5.](#) More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

2. Refer to [Figure 11.](#)

3.  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  condition to avoid thermal runaway for a diode on its own heatsink

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case	1.3	°C/W
		0.7	
R <sub>th(c)</sub>	Coupling	0.1	

**Table 4. Static electrical characteristics (per diode, at 25 °C unless otherwise specified)**

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = 70 V		7		µA
		T <sub>j</sub> = 125 °C			7		mA
		T <sub>j</sub> = 25 °C	V <sub>R</sub> = 100 V		13	45	µA
		T <sub>j</sub> = 125 °C			13	45	mA
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A		520		mV
		T <sub>j</sub> = 125 °C			435		
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A		620	700	
		T <sub>j</sub> = 125 °C			520	580	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 20 A		740	810	
		T <sub>j</sub> = 125 °C			605	665	

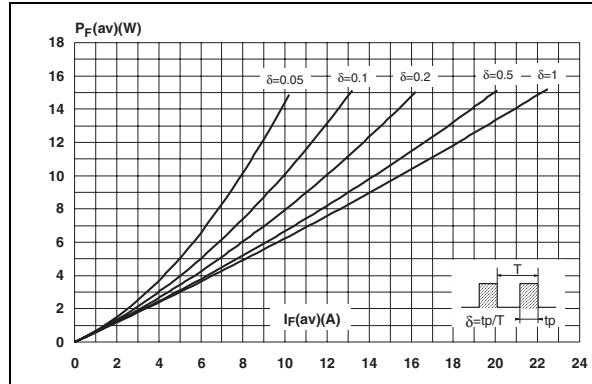
1. Pulse test: t<sub>p</sub> = 5 ms, δ < 2%

2. Pulse test: t<sub>p</sub> = 380 µs, δ < 2%

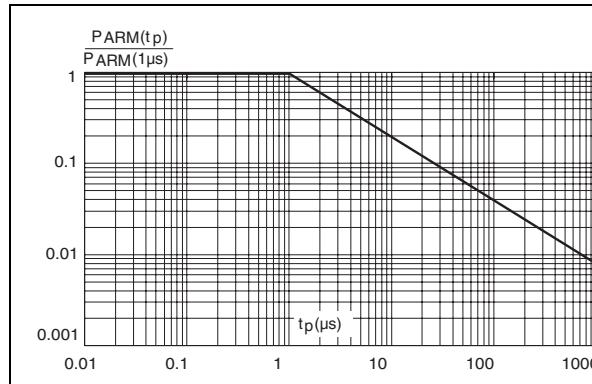
To evaluate the conduction losses use the following equation:

$$P = 0.580 \times I_{F(AV)} + 0.0043 \times I_{F(RMS)}^2$$

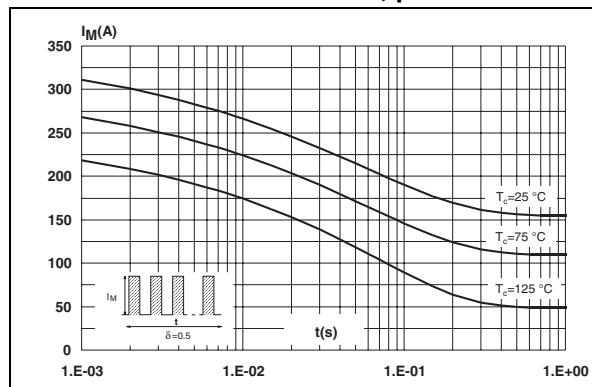
**Figure 2.** Average forward power dissipation versus average forward current (per diode)



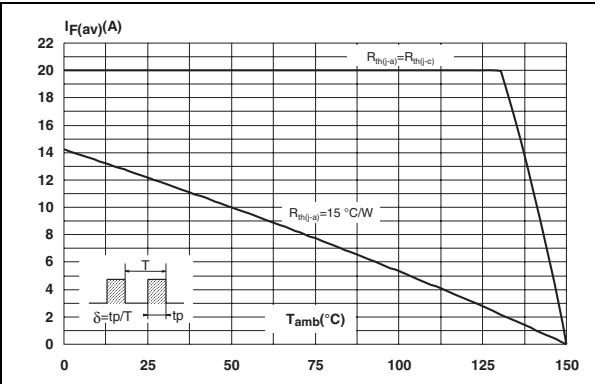
**Figure 4.** Normalized avalanche power derating versus pulse duration



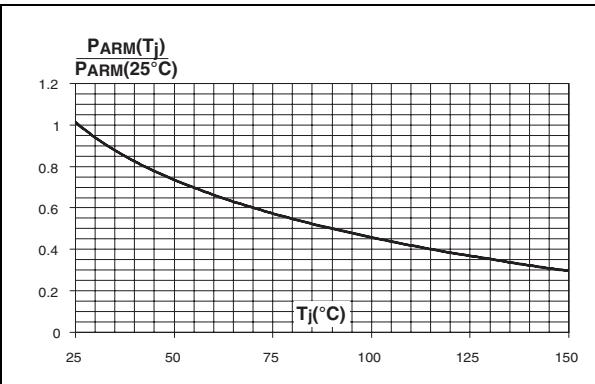
**Figure 6.** Non repetitive surge peak forward current versus overload duration, maximum values, per diode



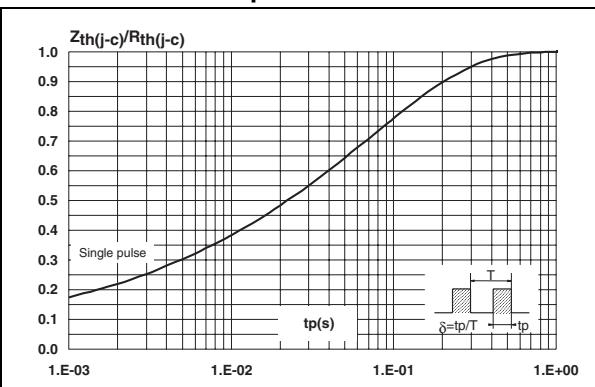
**Figure 3.** Average forward current versus ambient temperature ( $\delta = 0.5$ , per diode)



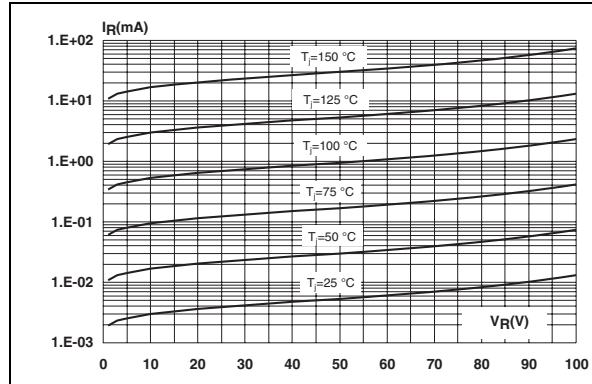
**Figure 5.** Normalized avalanche power derating versus junction temperature



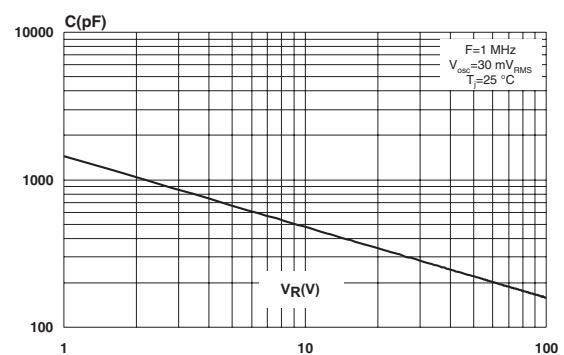
**Figure 7.** Relative variation of thermal impedance junction to case versus pulse duration



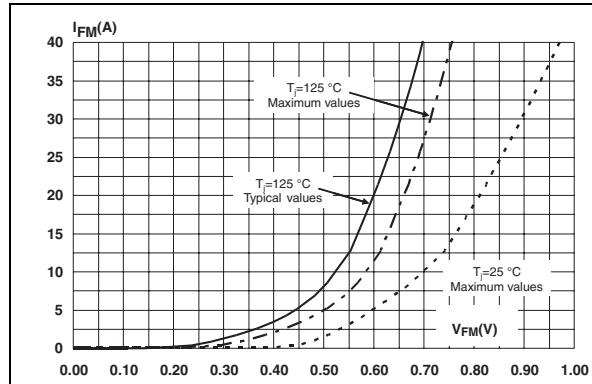
**Figure 8.** Reverse leakage current versus reverse voltage applied (typical values, per diode)



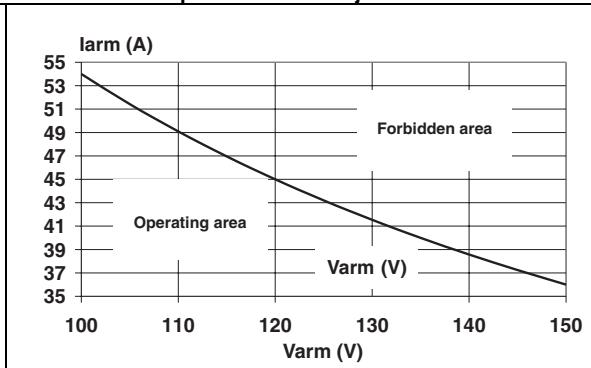
**Figure 9.** Junction capacitance versus reverse voltage applied (typical values, per diode)



**Figure 10.** Forward voltage drop versus forward current (per diode)



**Figure 11.** Reverse safe operating area ( $t_p < 1 \mu s$  and  $T_j < 150$  °C)



## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: C
- Recommended torque value: 0.4 to 0.6 N·m

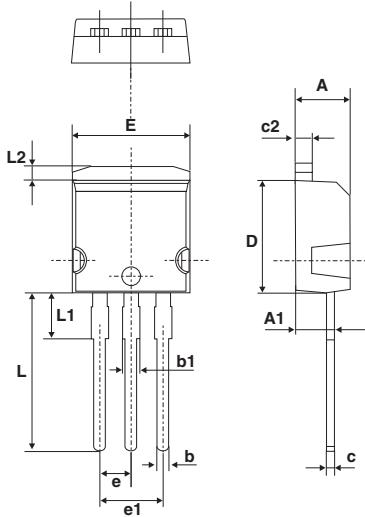
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

**Table 5. TO-220AB dimensions**

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
Øl	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	

**Table 6.** I<sup>2</sup>PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

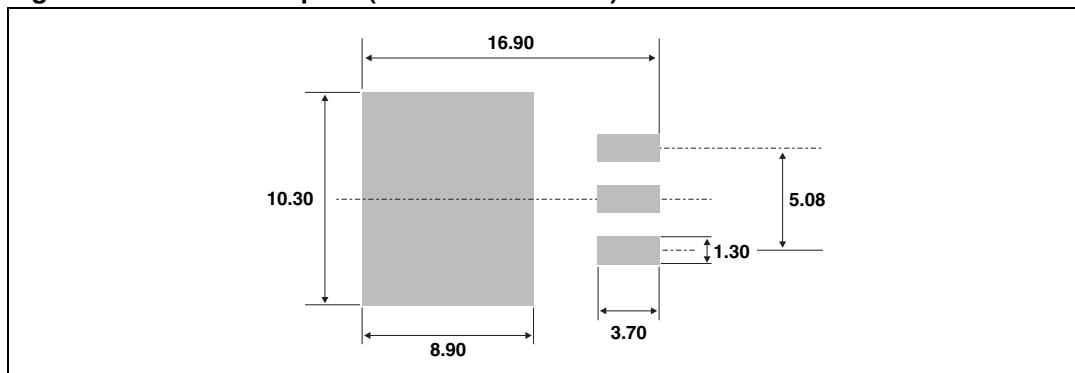


The technical drawing illustrates the I<sup>2</sup>PAK package with two views: a top view showing the lead configuration and a side view showing the profile. Various dimensions are labeled: L (total height), L1 (body height), L2 (lead height), E (lead pitch), c (lead thickness), b (lead width), b1 (lead width at base), e (lead thickness at base), e1 (lead thickness at top), A (width of the top flange), A1 (width of the bottom flange), c2 (lead spacing), and D (width of the body). The top view shows the leads extending downwards from the main body, and the side view shows the profile of the package with its various layers and lead configurations.

**Table 7.** D<sup>2</sup>PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

\* FLAT ZONE NO LESS THAN 2mm

**Figure 12.** D<sup>2</sup>PAK footprint (dimensions in mm)

### 3 Ordering information

**Table 8. Ordering information**

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS40SM100CT	PS40SM100CT	TO-220AB	2.2 g	50	Tube
STPS40SM100CR	PS40SM100CR	I <sup>2</sup> PAK	1.49 g	50	Tube
STPS40SM100CG	PS40SM100CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS40SM100CG-TR	PS40SM100CG	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel

### 4 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
25-Mar-2009	1	First issue

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